ABSTRACT

The present invention provides a single crystal wafer, wherein the main surface has a plane or a plane equivalent to a plane tilting with respect to a [100] axis of single crystal by angles of α ($0° < \alpha < 90°$) for the [011] direction, β ($0° < \beta < 90°$) for the [01-1] direction and γ ($0° \leqq \gamma < 45°$) for the [10-1] or [101] direction. Thus, a single crystal wafer that can sufficiently bear device production processes even with a small wafer thickness is provided and thereby loss of single crystal raw material is reduced. Further, by using such a wafer, MIS type semiconductor devices and solar cells are provided at a low cost.



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